



P-Channel Enhancement Mode Power MOSFET

Description

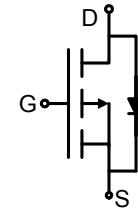
The PE2209A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -1.8V. This device is suitable for use as a load switch or in PWM applications.

General Features

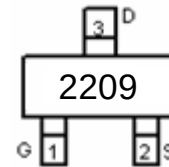
- $V_{DS} > -20V, I_D = -1.2A$
 $R_{DS(ON)} < 195m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 350m\Omega @ V_{GS} = -2.5V$
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch



Schematic diagram



Marking and pin assignment



SOT-23

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-1.2	A
Drain Current -Pulsed (Note 1)	I_{DM}	-3.5	A
Maximum Power Dissipation	P_D	0.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	178	$^\circ C/W$
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Electrical Characteristics ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA



Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-0.5A	-	160	195	mΩ
		V _{GS} =-2.5V, I _D =-0.4A	-	280	350	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-1A	4	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V, F=1.0MHz	-	210	-	PF
Output Capacitance	C _{oss}		-	54	-	PF
Reverse Transfer Capacitance	C _{rss}		-	27	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, R _L =5Ω V _{GS} =-4.5V,R _{GEN} =3Ω	-	10	-	nS
Turn-on Rise Time	t _r		-	5.0	-	nS
Turn-Off Delay Time	t _{d(off)}		-	21	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =-10V,I _D =-1A, V _{GS} =-4.5V	-	3.2	-	nC
Gate-Source Charge	Q _{gs}		-	0.5	-	nC
Gate-Drain Charge	Q _{gd}		-	0.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-2.0	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

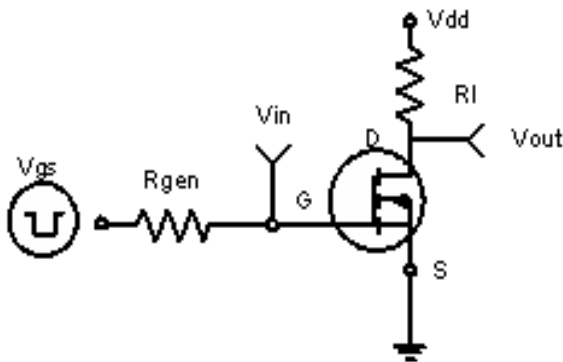


Figure 1: Switching Test Circuit

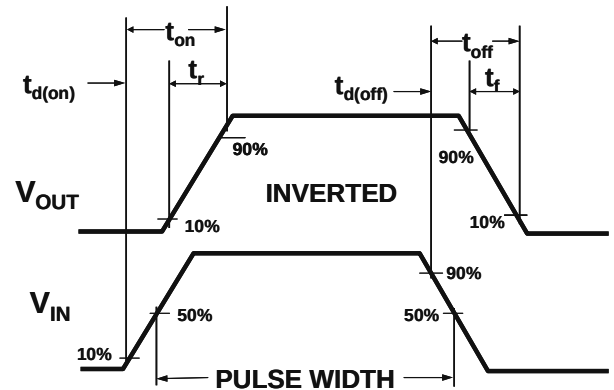


Figure 2: Switching Waveforms

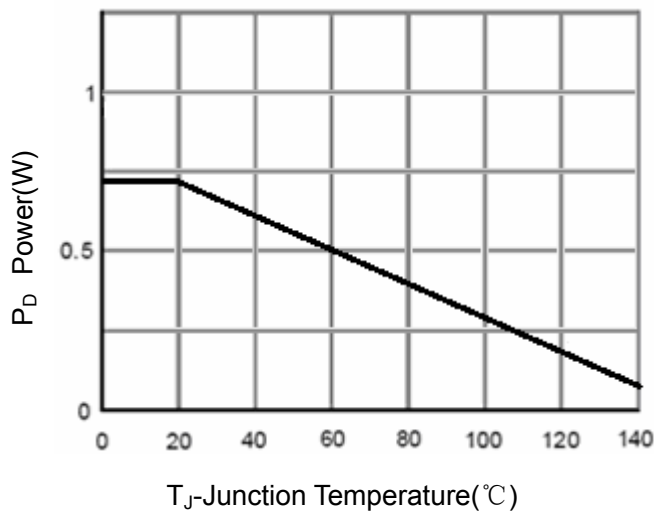


Figure 3: Power Dissipation

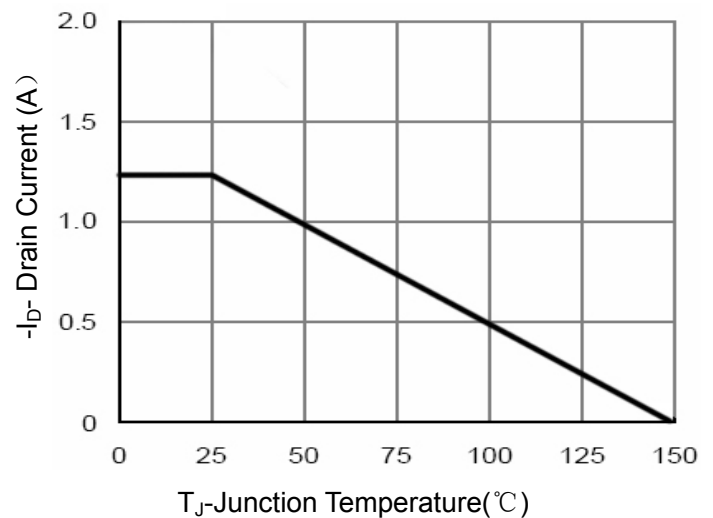


Figure 4: Drain Current

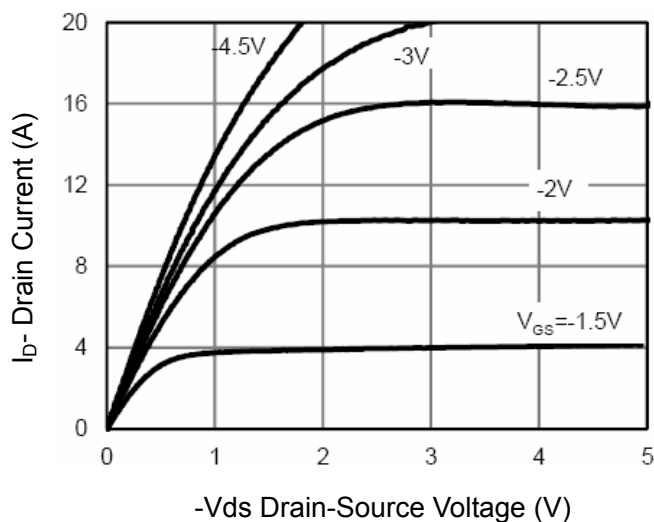


Figure 5: Output Characteristics

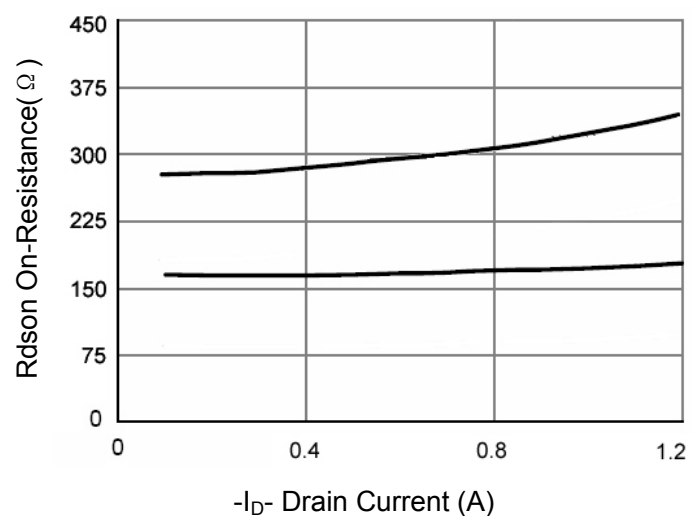


Figure 6: Drain-Source On-Resistance

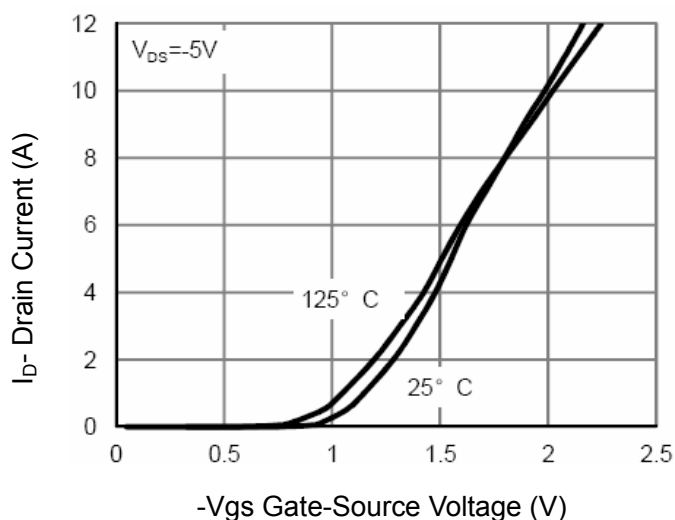


Figure 7 Transfer Characteristics

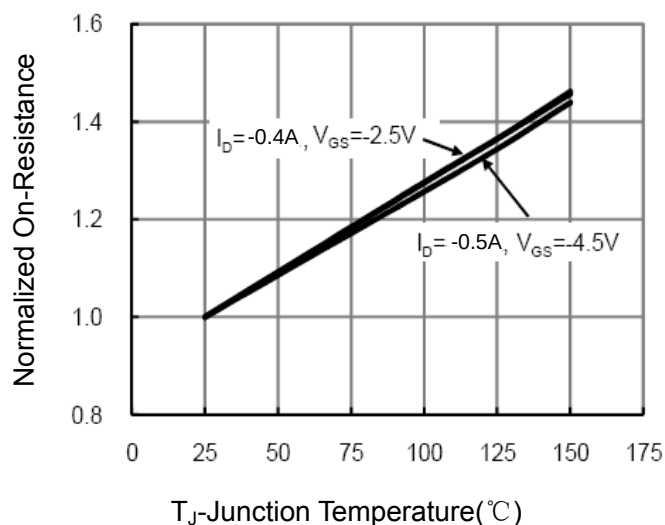


Figure 8 Drain-Source On-Resistance

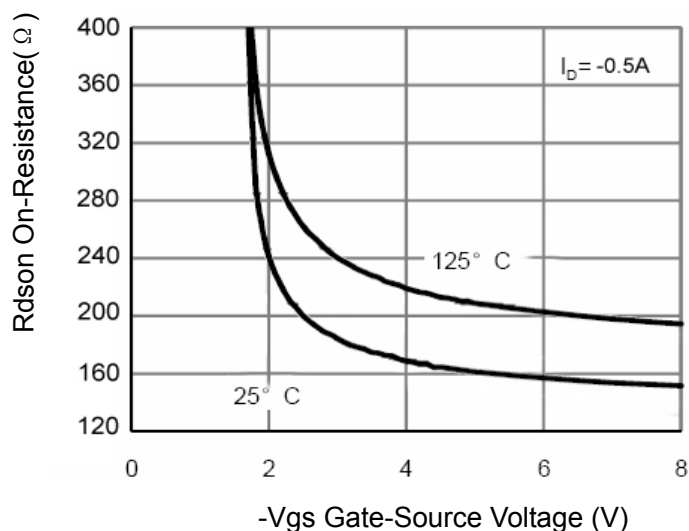


Figure 9 Rdson vs Vgs

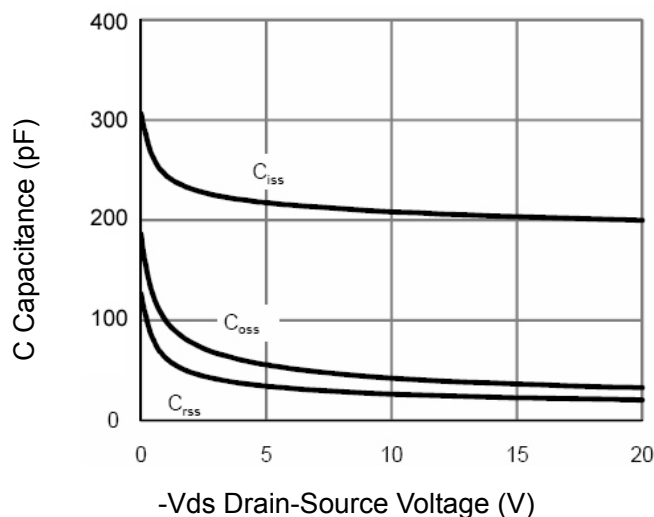


Figure 10 Capacitance vs Vds

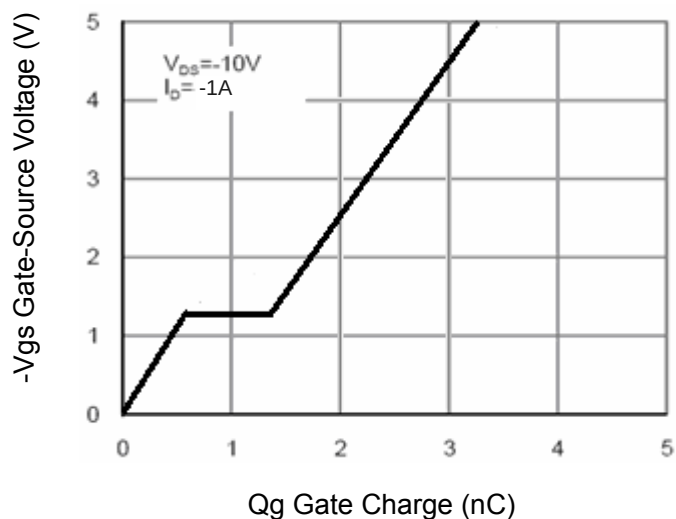


Figure 11 Gate Charge

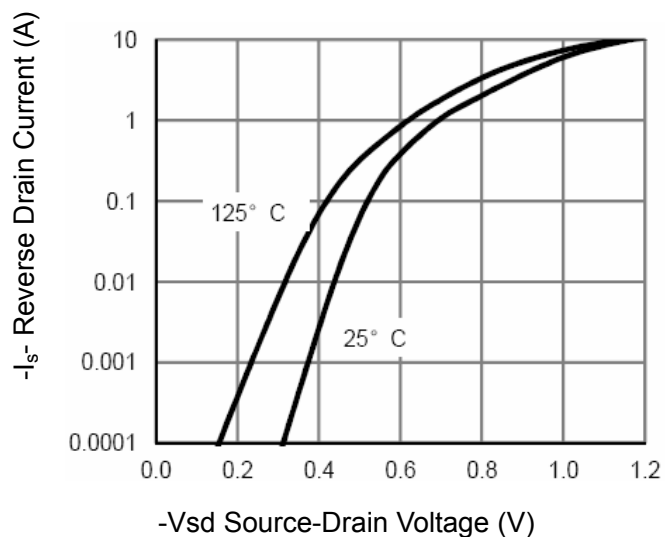


Figure 12 Source- Drain Diode Forward

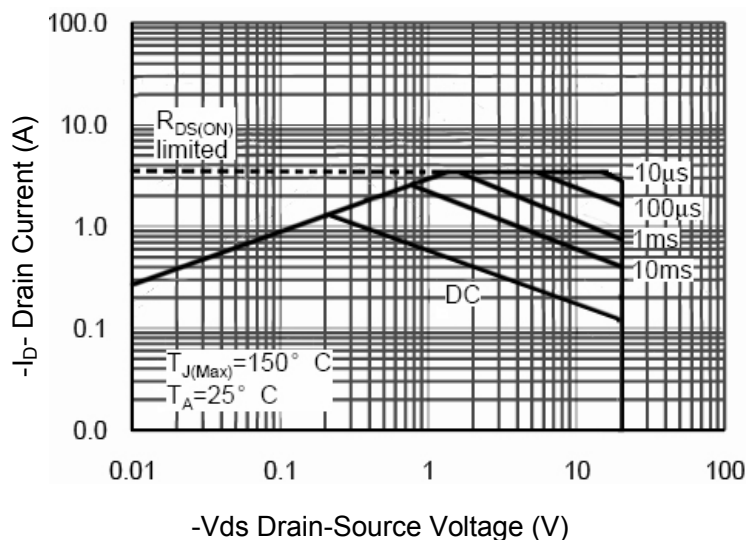


Figure 13 Safe Operation Area

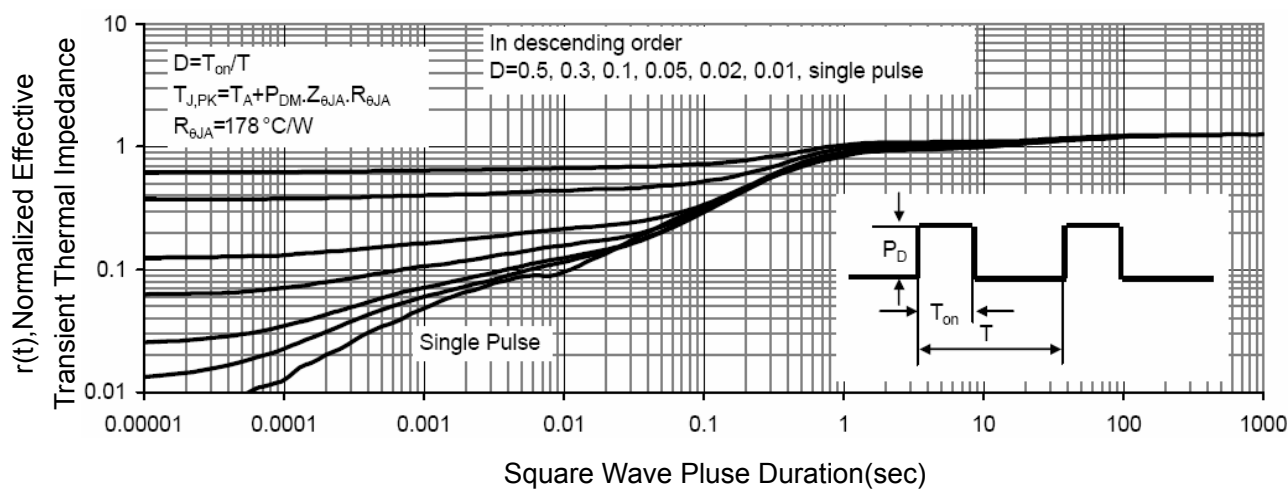
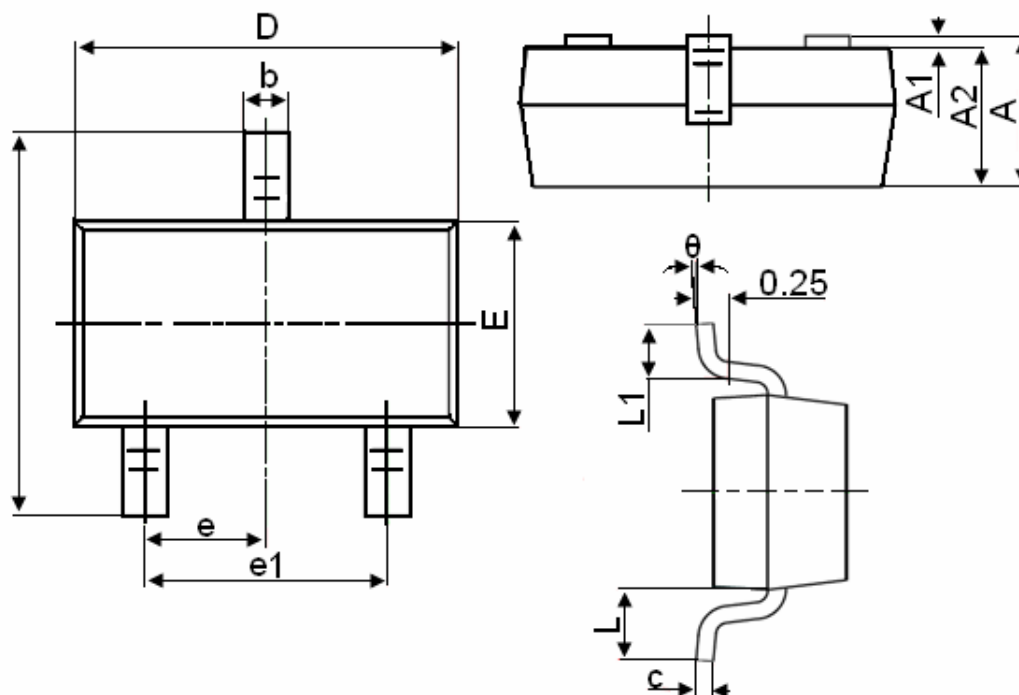


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°